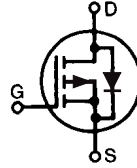


Standard Power MOSFET

P-Channel Enhancement Mode
Avalanche Rated

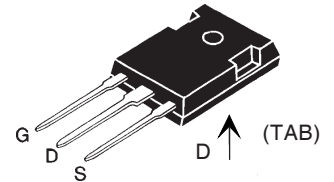
IXTH 11P50
IXTT 11P50

$V_{DSS} = -500 \text{ V}$
 $I_{D25} = -11 \text{ A}$
 $R_{DS(on)} = 0.75 \text{ } \Omega$

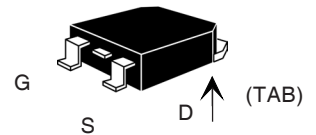


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	-500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	-500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	-11	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_J	-44	A
I_{AR}	$T_C = 25^\circ\text{C}$	-11	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-247 AD (IXTH)



TO-268 (IXTT) Case Style



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \text{ } \mu\text{A}$ BV_{DSS} Temperature Coefficient	-500	0.054	V %/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ } \mu\text{A}$ $V_{GS(th)}$ Temperature Coefficient	-3.0	-0.122	V %/K
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			-200 μA -1 mA
$R_{DS(on)}$	$V_{GS} = -10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ $R_{DS(on)}$ Temperature Coefficient			0.75 Ω 0.6 %/K

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

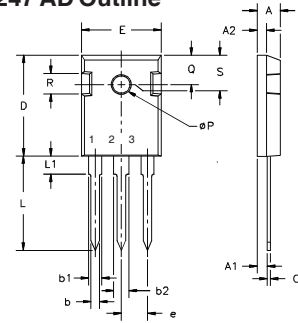
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = -10\text{ V}; I_D = I_{D25}$, pulse test	5	9	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		4700	pF
C_{oss}			430	pF
C_{rss}			135	pF
$t_{d(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 4.7\ \Omega$ (External)		33	ns
t_r			27	ns
$t_{d(off)}$			35	ns
t_f			35	ns
$Q_{G(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		130	nC
Q_{GS}			46	nC
Q_{GD}			92	nC
R_{thJC}	(TO-247)		0.42	K/W
R_{thCS}			0.25	K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
I_S	$V_{GS} = 0$	10P50 11P50		-10 -11	A A
I_{SM}	Repetitive; pulse width limited by T_{JM}	10P50 11P50		-40 -44	A A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			-3	V
t_{rr}	$I_F = I_S, di/dt = 100\text{ A}/\mu\text{s}$		500		ns

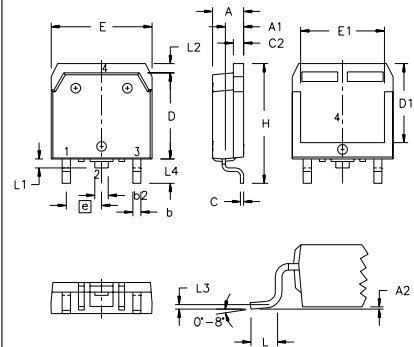
TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010 BSC		0.25 BSC	
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics @ 25 Deg. C

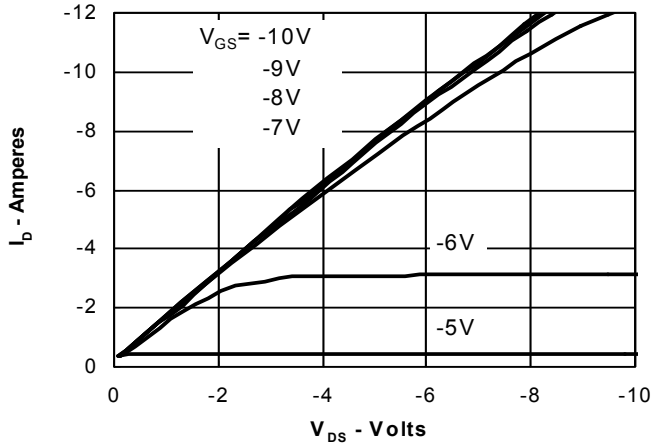


Fig. 2. Extended Output Characteristics @ 25 Deg. C

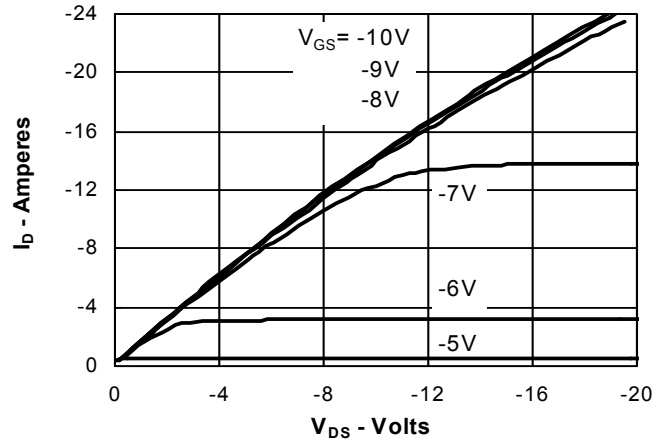


Fig. 3. Output Characteristics @ 125 Deg. C

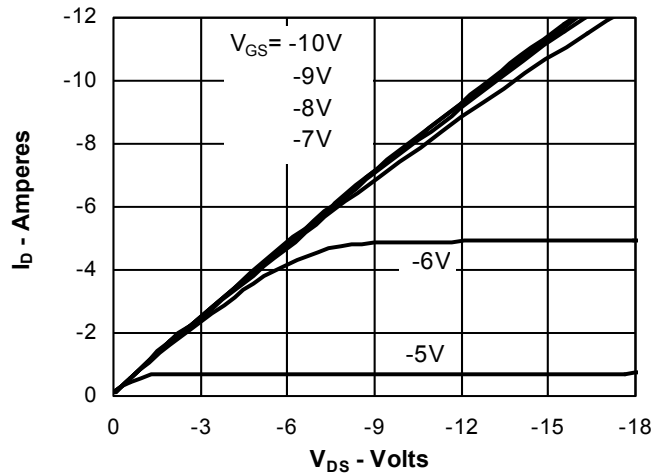


Fig. 4. R_{DS(ON)} Normalized to I_{D25} Value vs. Junction Temperature

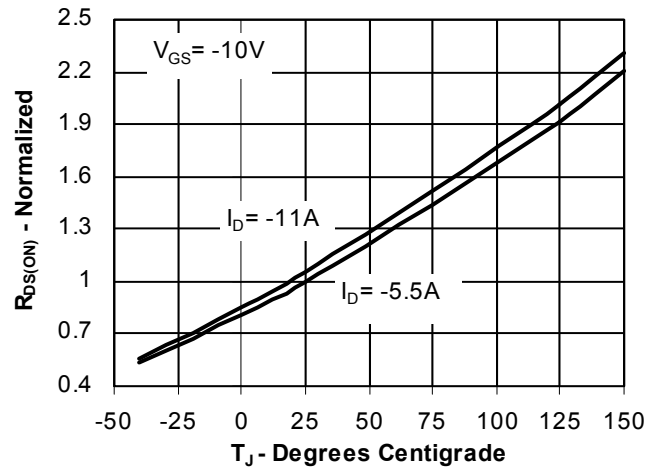


Fig. 5. R_{DS(ON)} Normalized to I_{D25} Value vs. I_D

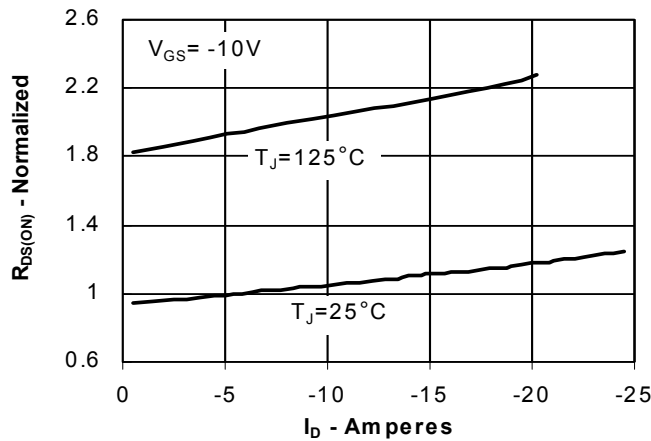


Fig. 6. Input Admittance

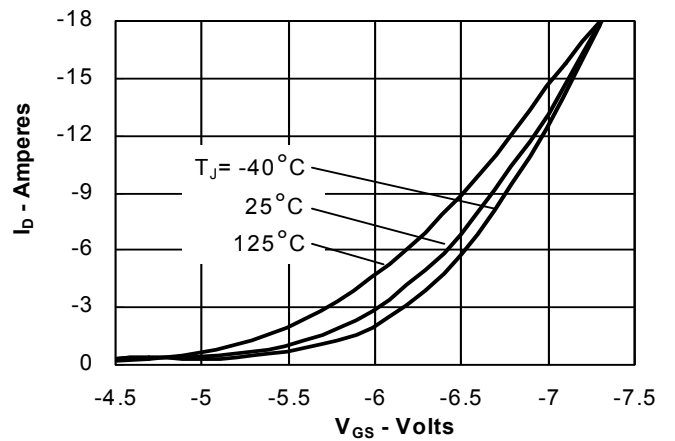


Fig. 7. Transconductance

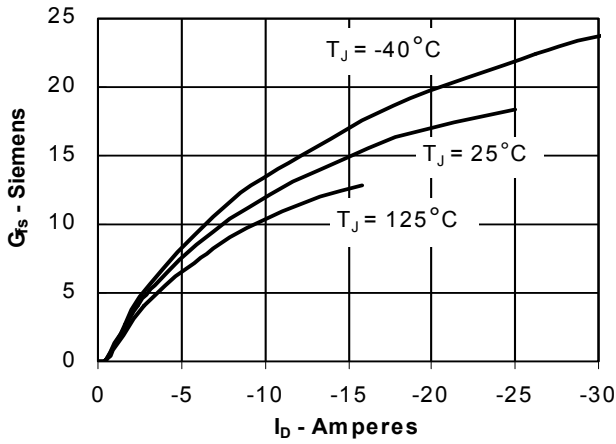


Fig. 8. Source Current vs. Source-To-Drain Voltage

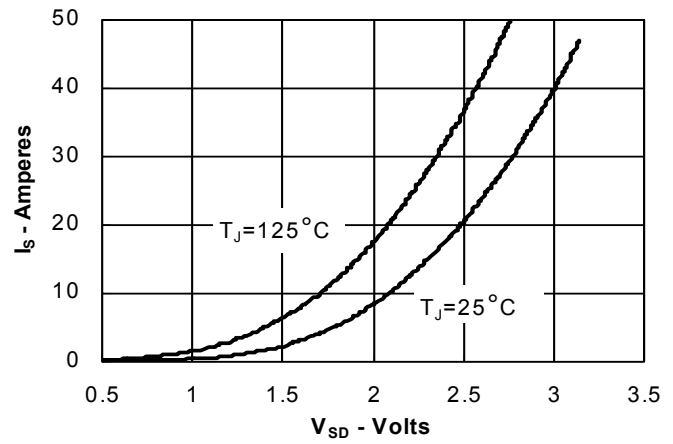


Fig. 9. Gate Charge

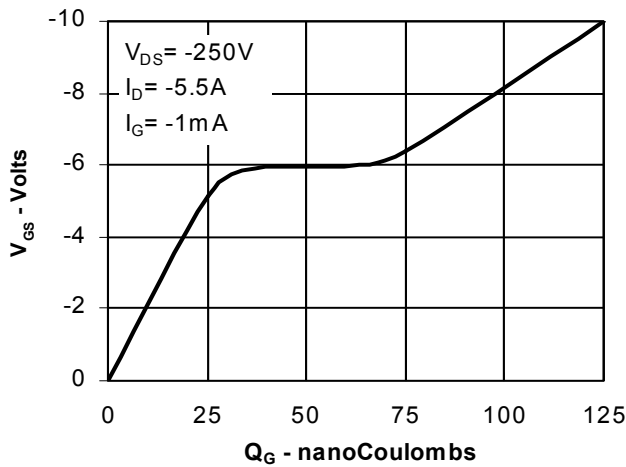


Fig. 10. Capacitance

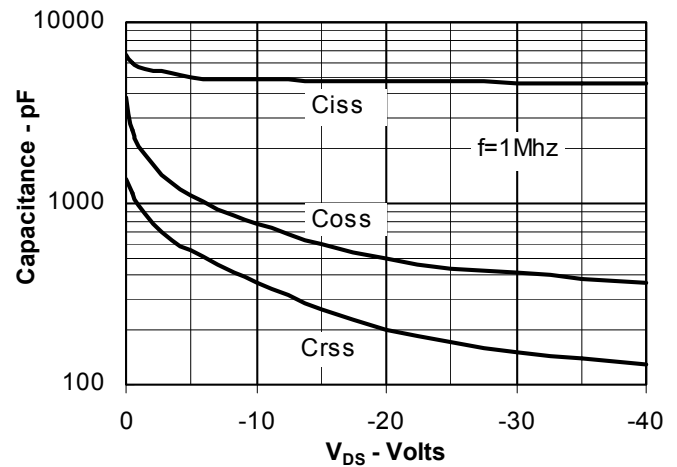


Fig. 14. Maximum Transient Thermal Resistance

